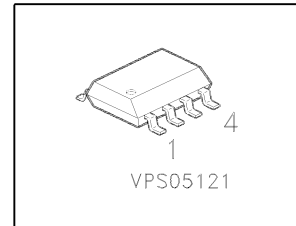
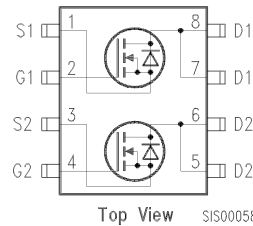


SIPMOS® Small-Signal-Transistor
Features

- Dual N Channel
- Enhancement mode
- Avalanche rated
- Logic Level
- dv/dt rated
- Pb-free lead plating; RoHS compliant

Product Summary

Drain source voltage	V_{DS}	60	V
Drain-Source on-state resistance	$R_{DS(on)}$	0.15	Ω
Continuous drain current	I_D	2.6	A



Type	Package	Marking
BSO 615N	SO 8	615N

Maximum Ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current, <i>one channel active</i>	I_D	2.6	A
Pulsed drain current, <i>one channel active</i>	I_{Dpulse}	10.4	
$T_A = 25\text{ °C}$			
Avalanche energy, single pulse	E_{AS}	60	mJ
$I_D = 2.6\text{ A}, V_{DD} = 25\text{ V}, R_{GS} = 25\ \Omega$			
Avalanche current, periodic limited by T_{jmax}	I_{AR}	2.6	A
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	0.18	mJ
Reverse diode dv/dt	dv/dt	6	kV/ μ s
$I_S = 2.6\text{ A}, V_{DS} = 40\text{ V}, di/dt = 200\text{ A}/\mu\text{s}, T_{jmax} = 150\text{ °C}$			
Gate source voltage	V_{GS}	± 20	V
Power dissipation, <i>one channel active</i>	P_{tot}	2	W
$T_A = 25\text{ °C}$			
Operating temperature	T_j	-55 ... +150	°C
Storage temperature	T_{stg}	-55 ... +150	
IEC climatic category; DIN IEC 68-1		55/150/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point	R_{thJS}	-	-	35	K/W
Thermal resistance @ 10 sec., min. footprint	$R_{th(JA)}$	-	-	100	
Thermal resistance @ 10 sec., 6 cm ² cooling area ¹⁾	$R_{th(JA)}$	-	-	62.5	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$	$V_{(BR)DSS}$	60	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 20\text{ }\mu\text{A}$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$ $V_{DS} = 60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	I_{DSS}	-	0.1 10	1 100	μA
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	10	100	
Drain-Source on-state resistance $V_{GS} = 4.5\text{ V}$, $I_D = 2.6\text{ A}$	$R_{DS(on)}$	-	0.12	0.15	Ω

¹ Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 2.6$ A	g_{fs}	2.4	5.5	-	S
Input capacitance $V_{GS} = 0$ V, $V_{DS} = 25$ V, $f = 1$ MHz	C_{iss}	-	300	380	pF
Output capacitance $V_{GS} = 0$ V, $V_{DS} = 25$ V, $f = 1$ MHz	C_{oss}	-	90	120	
Reverse transfer capacitance $V_{GS} = 0$ V, $V_{DS} = 25$ V, $f = 1$ MHz	C_{rss}	-	50	65	
Turn-on delay time $V_{DD} = 30$ V, $V_{GS} = 4.5$ V, $I_D = 2.6$ A, $R_G = 16$ Ω	$t_{d(on)}$	-	12	20	ns
Rise time $V_{DD} = 30$ V, $V_{GS} = 4.5$ V, $I_D = 2.6$ A, $R_G = 16$ Ω	t_r	-	15	25	
Turn-off delay time $V_{DD} = 30$ V, $V_{GS} = 4.5$ V, $I_D = 2.6$ A, $R_G = 16$ Ω	$t_{d(off)}$	-	20	30	
Fall time $V_{DD} = 30$ V, $V_{GS} = 4.5$ V, $I_D = 2.6$ A, $R_G = 16$ Ω	t_f	-	15	25	

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

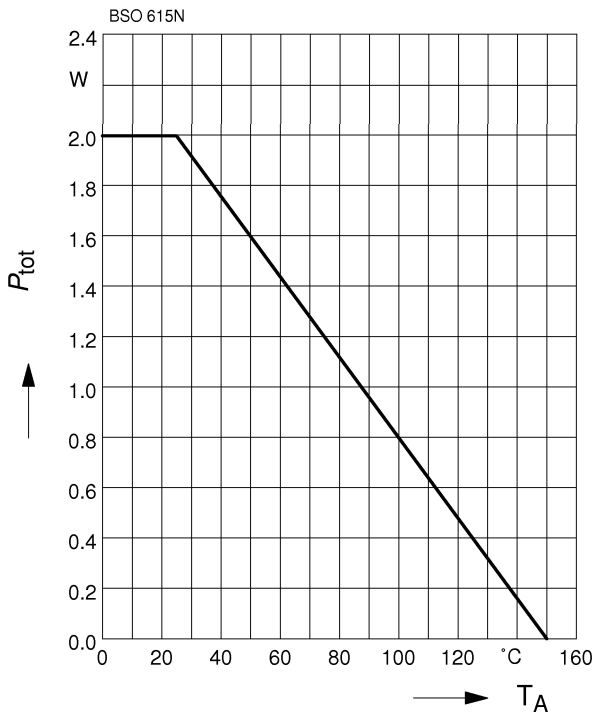
Parameter at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Gate charge at threshold $V_{DD} = 40\text{ V}$, $I_D = 0.1\text{ A}$, $V_{GS} = 1\text{ V}$	$Q_{G(th)}$	-	0.4	0.6	nC
Gate charge at $V_{GS}=5\text{V}$ $V_{DD} = 40\text{ V}$, $I_D = 2.6\text{ A}$, $V_{GS} = 0\text{ to }5\text{ V}$	$Q_{g(5)}$	-	7	10	
Gate charge total $V_{DD} = 40\text{ V}$, $I_D = 2.6\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$	Q_g	-	14	20	nC
Gate plateau voltage $V_{DD} = 40\text{ V}$, $I_D = 2.6\text{ A}$	$V_{(plateau)}$	-	3.6	-	V

Reverse Diode

Inverse diode continuous forward current $T_A = 25\text{ }^\circ\text{C}$	I_S	-	-	2.6	A
Inverse diode direct current, pulsed $T_A = 25\text{ }^\circ\text{C}$	I_{SM}	-	-	10.4	
Inverse diode forward voltage $V_{GS} = 0\text{ V}$, $I_F = 5.2\text{ A}$	V_{SD}	-	0.95	1.2	V
Reverse recovery time $V_R = 30\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	50	75	ns
Reverse recovery charge $V_R = 30\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	0.1	0.15	μC

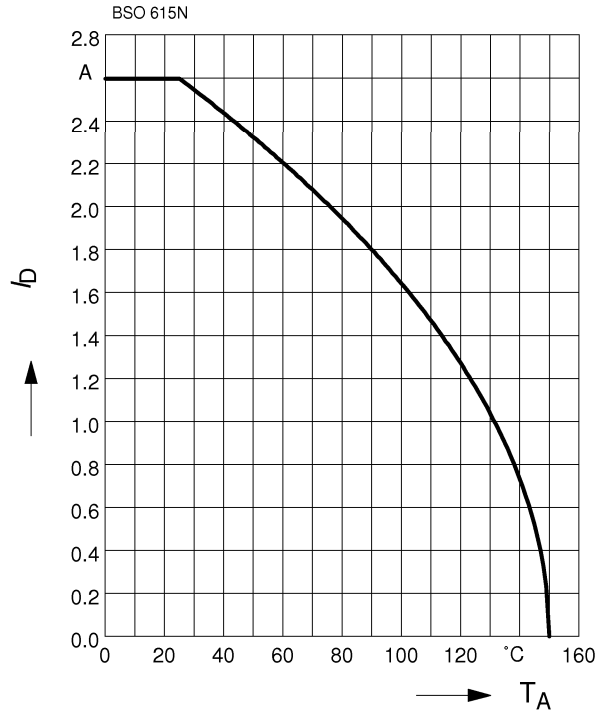
Power Dissipation

$P_{tot} = f(T_A), V_{GS} = 4,5 V$



Drain current

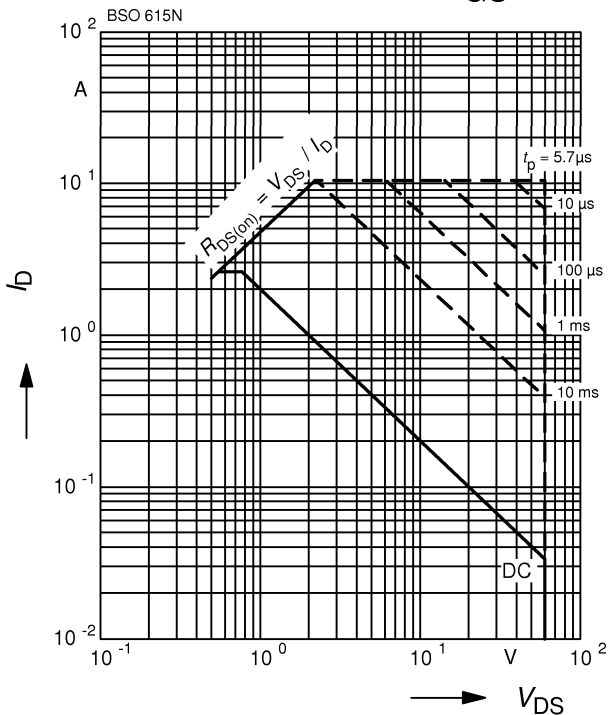
$I_D = f(T_A), V_{GS} = 4,5 V$



Safe operating area

$I_D = f(V_{DS})$

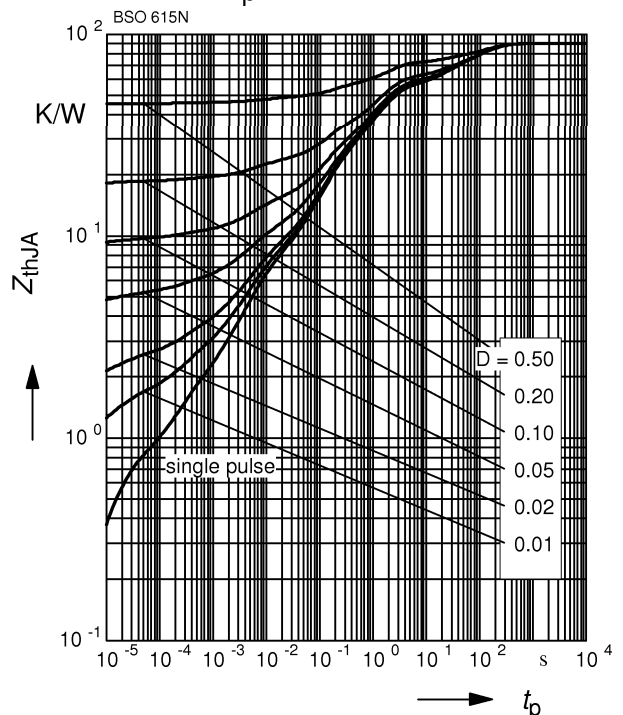
parameter : $D = 0, T_A = 25\text{ }^\circ\text{C}, V_{GS} = 4,5 V$



Transient thermal impedance

$Z_{thJA} = f(t_p)$

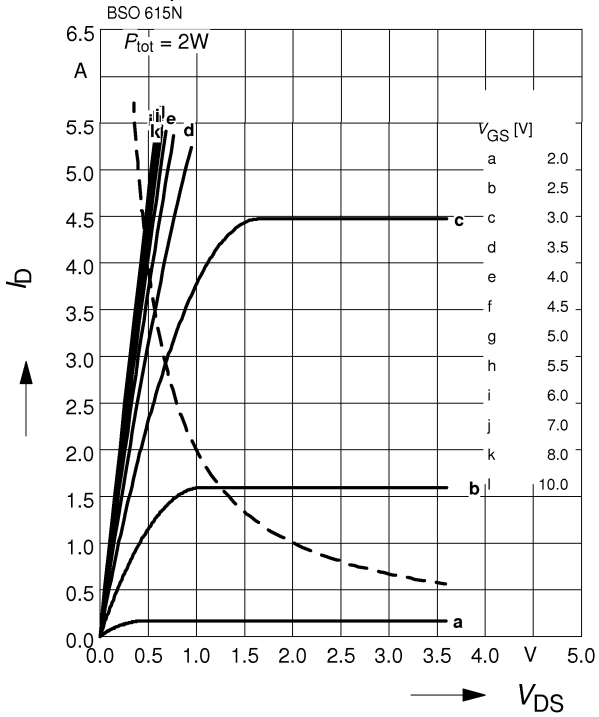
parameter : $D = t_p/T$



Typ. output characteristics

$I_D = f(V_{DS})$

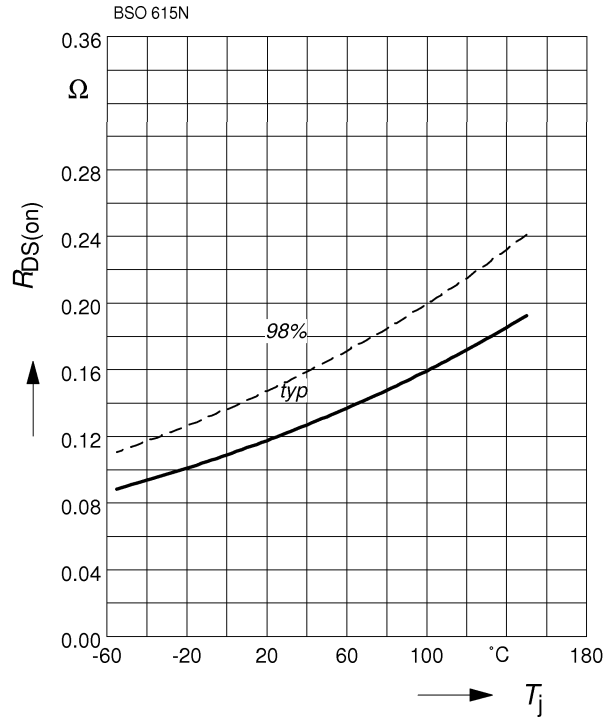
parameter: $t_p = 80 \mu s$



Drain-source on-resistance

$R_{DS(on)} = f(T_j)$

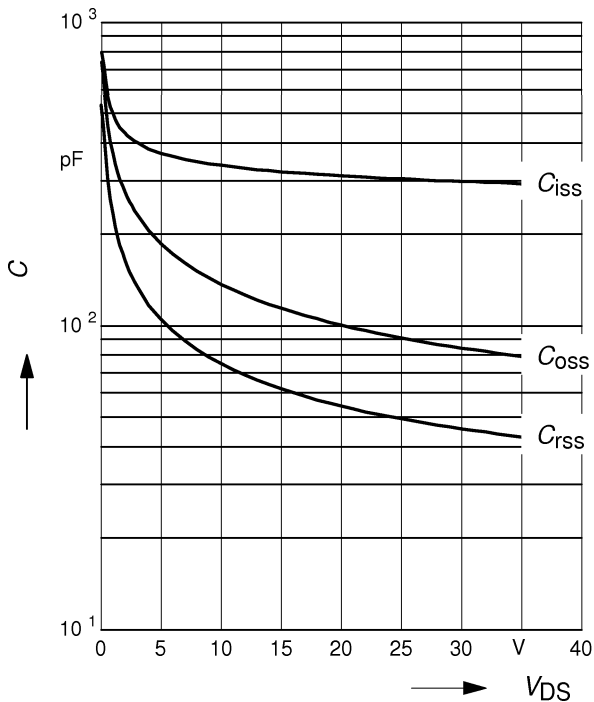
parameter : $I_D = 2.6 A, V_{GS} = 4.5 V$



Typ. capacitances

$C = f(V_{DS})$

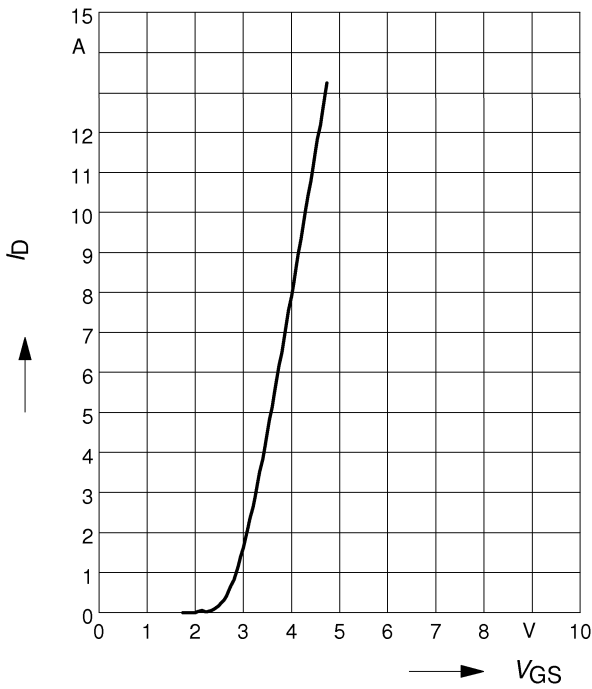
parameter: $V_{GS} = 0 V, f = 1 MHz$



Typ. transfer characteristics $I_D = f(V_{GS})$

parameter: $t_p = 80 \mu s$

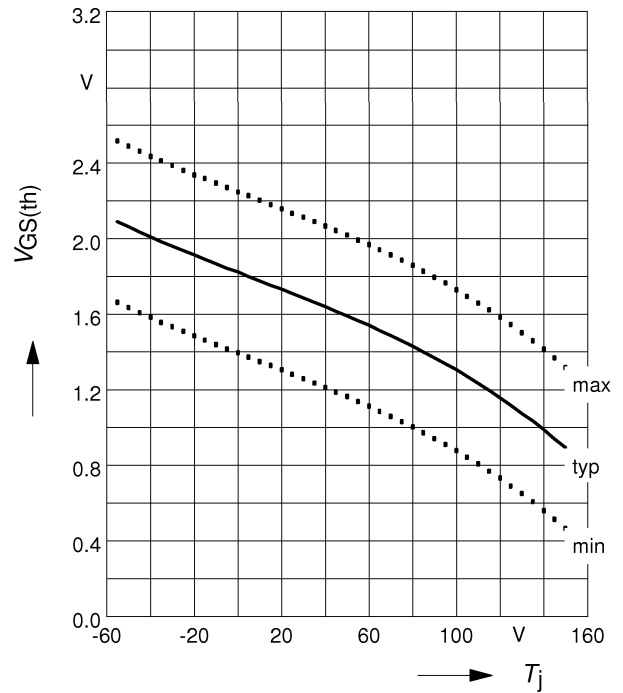
$V_{DS} \geq 2 \times I_D \times R_{DS(on) \max}$



Gate threshold voltage $V_{GS(th)} = f(T_j)$

$V_{GS(th)} = f(T_j)$

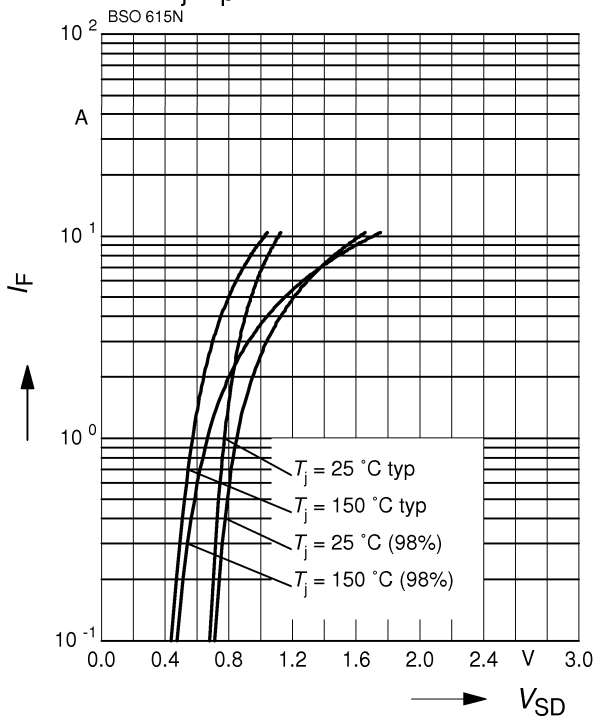
parameter: $V_{GS} = V_{DS}, I_D = 20 \mu A$



Forward characteristics of reverse diode $I_F = f(V_{SD})$

$I_F = f(V_{SD})$

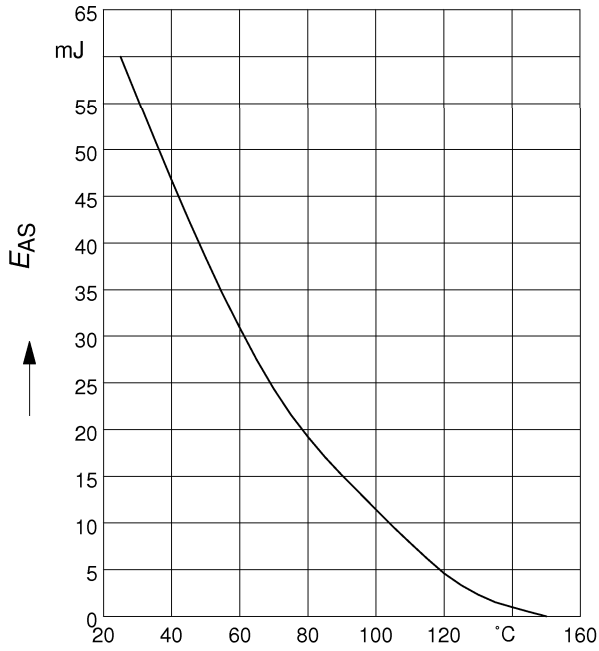
parameter: $T_j, t_p = 80 \mu s$



Avalanche Energy $E_{AS} = f(T_j)$

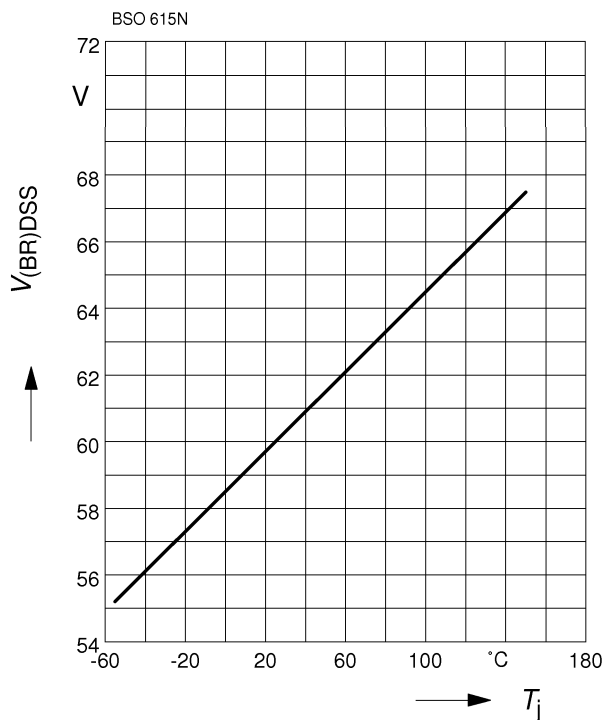
parameter: $I_D = 2.6 \text{ A}$, $V_{DD} = 25 \text{ V}$

$R_{GS} = 25 \Omega$



Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$



Typ. gate charge

$V_{GS} = f(Q_{Gate})$

parameter: $I_{D \text{ puls}} = 2.6 \text{ A}$

